

MC74HC574A

Octal 3-State Noninverting D Flip-Flop High-Performance Silicon-Gate CMOS

The MC74HC574A is identical in pinout to the LS574. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

Data meeting the set-up time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HC574A is identical in function to the HC374A but has the flip-flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

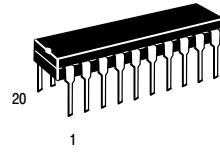
- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates



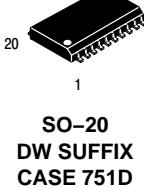
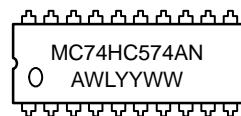
ON Semiconductor

<http://onsemi.com>

MARKING DIAGRAMS



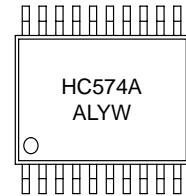
PDIP-20
N SUFFIX
CASE 783



SO-20
DW SUFFIX
CASE 751D



TSSOP-20
DT SUFFIX
CASE 948E



A = Assembly Location

L, WL = Wafer Lot

Y, YY = Year

W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HC574AN	PDIP-20	1440/Box
MC74HC574ADW	SOIC-WIDE	38/Rail
MC74HC574ADWR2	SOIC-WIDE	1000/Reel
MC74HC574ADT	TSSOP-20	75/Rail
MC74HC574ADTR2	TSSOP-20	2500/Reel

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OUTPUT	1•	20	V _{CC}
ENABLE			
D0	2	19	Q0
D1	3	18	Q1
D2	4	17	Q2
D3	5	16	Q3
D4	6	15	Q4
D5	7	14	Q5
D6	8	13	Q6
D7	9	12	Q7
GND	10	11	CLOCK

FUNCTION TABLE

Inputs		Output	
OE	Clock	D	Q
L	/	H	H
L	/	L	L
L	L,H,/L	X	No Change
H	X	X	Z

X = Don't Care

Z = High Impedance

Figure 24. Pin Assignment

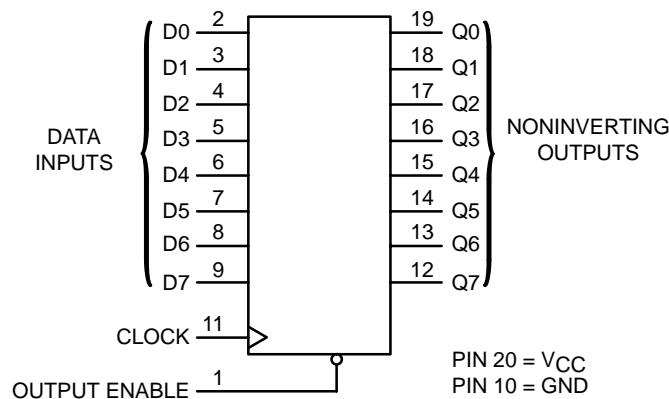


Figure 25. Logic Diagram

Design Criteria	Value	Units
Internal Gate Count*	66.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	µW
Speed Power Product	0.0075	pJ

*Equivalent to a two-input NAND gate.

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MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	– 0.5 to + 7.0	V
V _I	DC Input Voltage	– 0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage (Note 2)	– 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 35	mA
I _O	DC Output Sink Current	± 35	mA
I _{CC}	DC Supply Current per Supply Pin	± 75	mA
I _{GND}	DC Ground Current per Ground Pin	± 75	mA
T _{TSG}	Storage Temperature Range	– 65 to + 150	C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	C
T _J	Junction Temperature under Bias	+ 150	C
θ _{JA}	Thermal Resistance	PDIP SOIC TSSOP	67 96 128
P _D	Power Dissipation in Still Air at 85 C	PDIP SOIC TSSOP	750 500 450
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL-94-VO (0.125 in)
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	>4000 >300 >1000
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85 C (Note 6)	± 300	mA

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied.
2. I_O absolute maximum rating must be observed.
3. Tested to EIA/JESD22-A114-A.
4. Tested to EIA/JESD22-A115-A.
5. Tested to JESD22-C101-A.
6. Tested to EIA/JESD78.
7. For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _I , V _O	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	– 55	+ 125	C
t _r , t _f	Input Rise and Fall Time (Figure 26) V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

8. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				–55 to 25°C	≤ 85°C	≤ 125°C	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1\text{ V}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1\text{ V}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \leq 2.4\text{ mA}$ $ I_{out} \leq 6.0\text{ mA}$ $ I_{out} \leq 7.8\text{ mA}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	V
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IL}$ $ I_{out} \leq 2.4\text{ mA}$ $ I_{out} \leq 6.0\text{ mA}$ $ I_{out} \leq 7.8\text{ mA}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\text{ }\mu\text{A}$	6.0	4.0	40	160	μA

9. Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$; Input $t_r = t_f = 6.0 \text{ ns}$)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			-55 to 25°C	≤ 85°C	≤ 125°C	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 26 and 29)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Clock to Q (Figures 26 and 29)	2.0 3.0 4.5 6.0	160 105 32 27	200 145 40 34	240 190 48 41	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 27 and 30)	2.0 3.0 4.5 6.0	150 100 30 26	190 125 38 33	225 150 45 38	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 27 and 30)	2.0 3.0 4.5 6.0	140 90 28 24	175 120 35 30	210 140 42 36	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, any Output (Figures 26 and 29)	2.0 3.0 4.5 6.0	60 27 12 10	75 32 15 13	90 36 18 15	ns
C_{in}	Maximum Input Capacitance		10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance, Output in High-Impedance State		15	15	15	pF

10. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

CPD	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$		pF
		24		

*Used to determine the no-load dynamic power consumption: $P_D = CPD V_{CC}^2 f + ICC V_{CC}$. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS ($C_L = 50 \text{ pF}$; Input $t_r = t_f = 6.0 \text{ ns}$)

Symbol	Parameter	Figure	V_{CC} Volts	Guaranteed Limit					Unit	
				-55 to 25°C		≤ 85°C		≤ 125°C		
				Min	Max	Min	Max	Min	Max	
t_{su}	Minimum Setup Time, Data to Clock	28	2.0 3.0 4.6 6.0	50 40 10 9.0		65 50 13 11		75 60 15 13		ns
t_h	Minimum Hold Time, Clock to Data	28	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t_w	Minimum Pulse Width, Clock	26	2.0 3.0 4.5 6.0	75 60 15 13		95 80 19 16		110 90 22 19		ns
t_r, t_f	Maximum Input Rise and Fall Times	26	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns

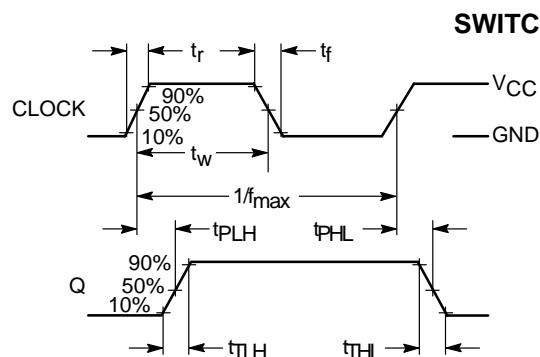


Figure 26.

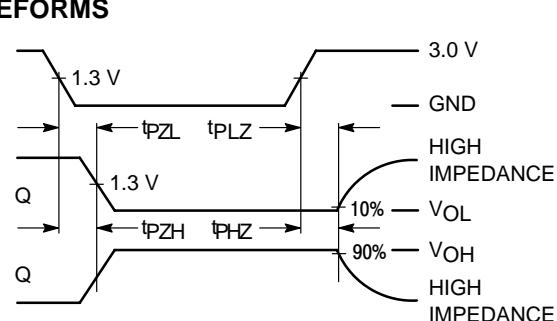


Figure 27.

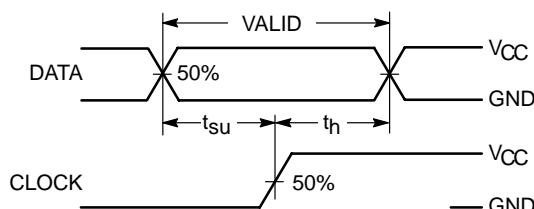
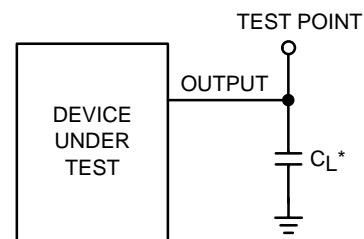
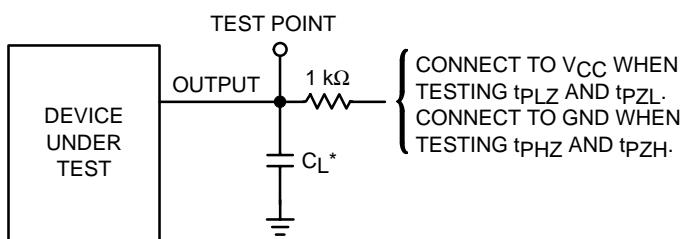


Figure 28.



*Includes all probe and jig capacitance.

Figure 29.



*Includes all probe and jig capacitance.

Figure 30. Test Circuit

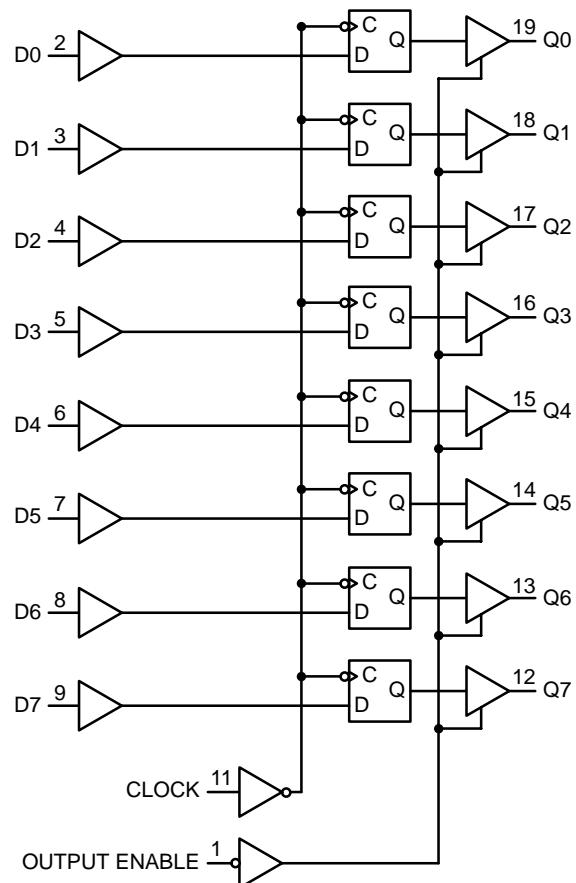


Figure 31. Expanded Logic Diagram